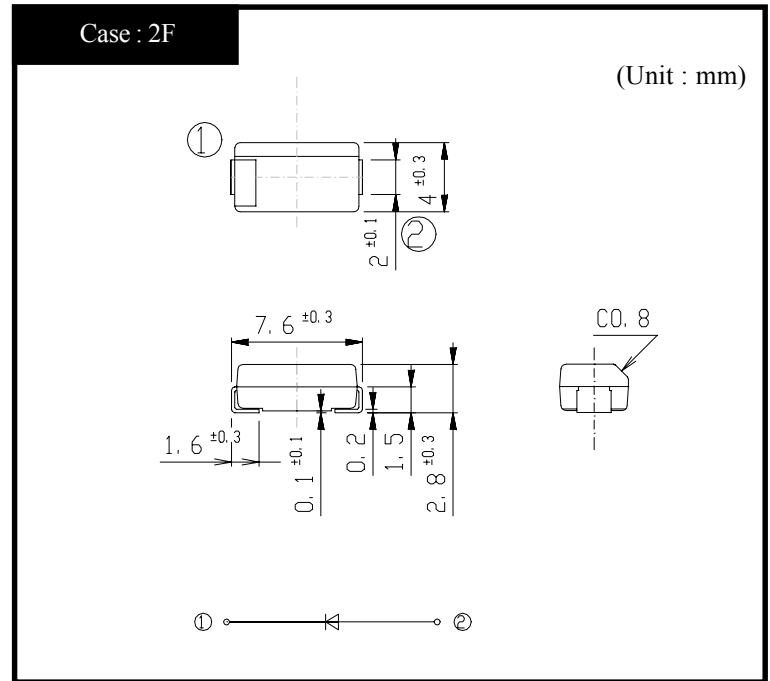


# KP4N12

## OUTLINE DIMENSIONS



## RATINGS

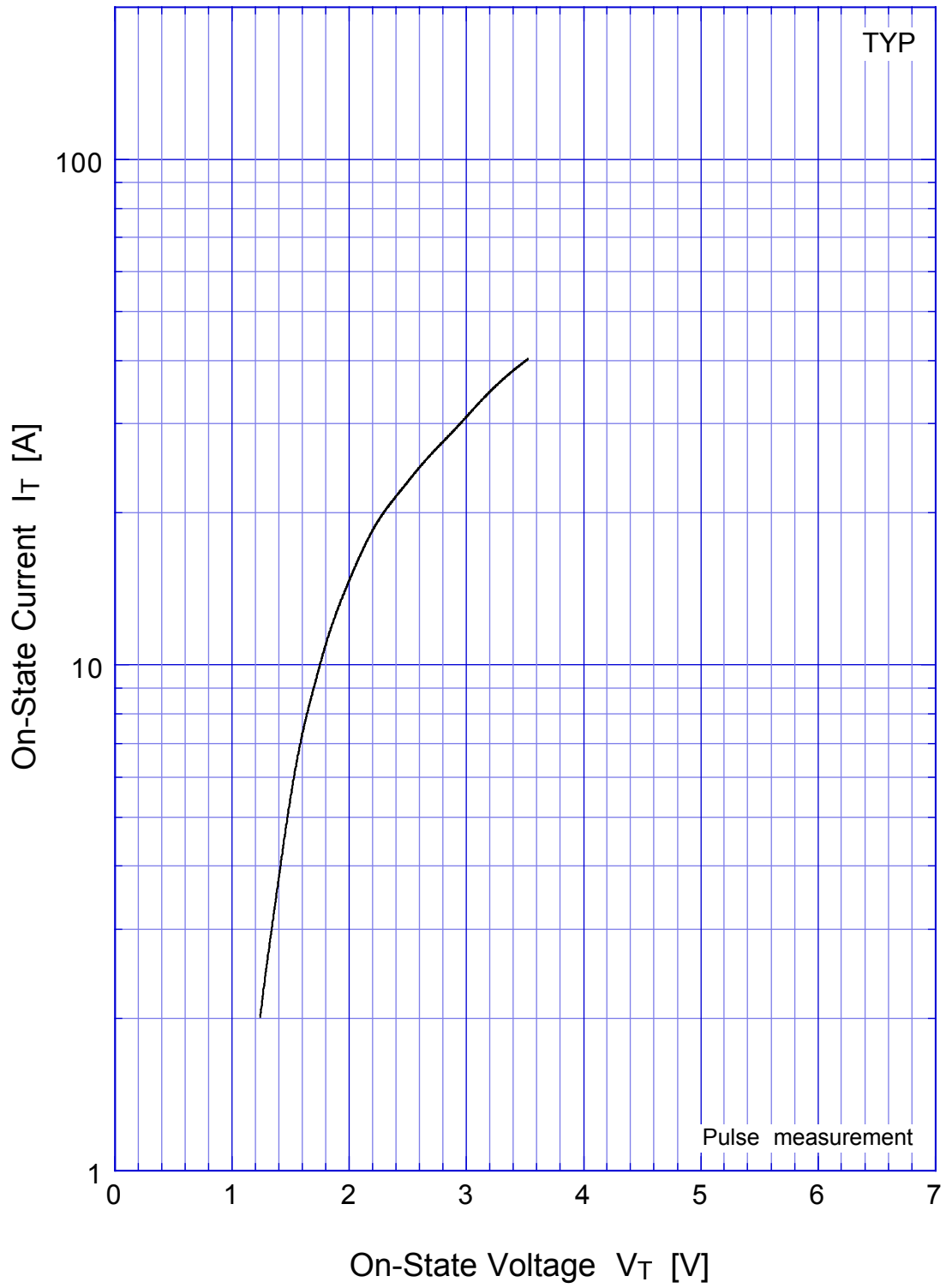
### ● Absolute Maximum Ratings

Item	Symbol	Conditions	Ratings	Unit
Storage Temperature	T <sub>stg</sub>		-40~125	°C
Junction Temperature	T <sub>j</sub>		125	°C
Maximum Off-State Voltage	V <sub>DRM</sub>		100	V
Surge On-State Current	I <sub>TSM</sub>	10/1000 μs, Non-repetitive	40	A
		10/200 μs, Non-repetitive	60	
		8/20 μs, Non-repetitive	150	

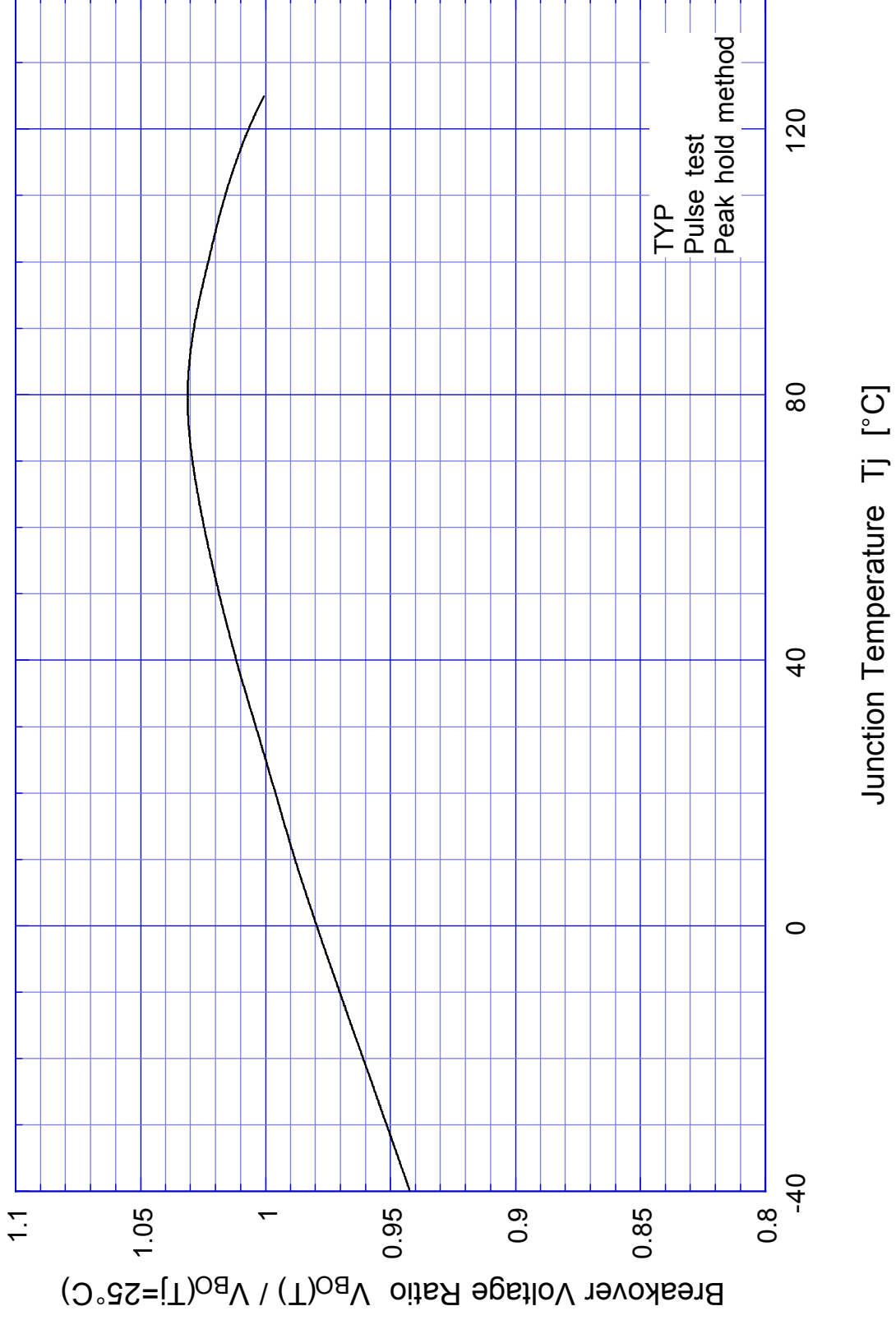
### ● Electrical Characteristics (Tl=25°C)

Item	Symbol	Conditions	Ratings	Unit
Breakover Voltage	V <sub>BO</sub>	Pulse measurement (Peak hold)	Min 110	V
Off-State Current	I <sub>DRM</sub>	V <sub>D</sub> = V <sub>DRM</sub>	Max 10	μA
Holding Current	I <sub>H</sub>	Pulse measurement	Min 100	mA
On-State Voltage	V <sub>T</sub>	I <sub>T</sub> = 2A	TYP 1.25	V
Junction Capacitance	C <sub>j</sub>	f = 1kHz OSC = 1V, V <sub>D</sub> = 50V	Max 50	pF
Clamping Voltage	V <sub>CL</sub>	dv/dt = 100V/μs	Max 135	V

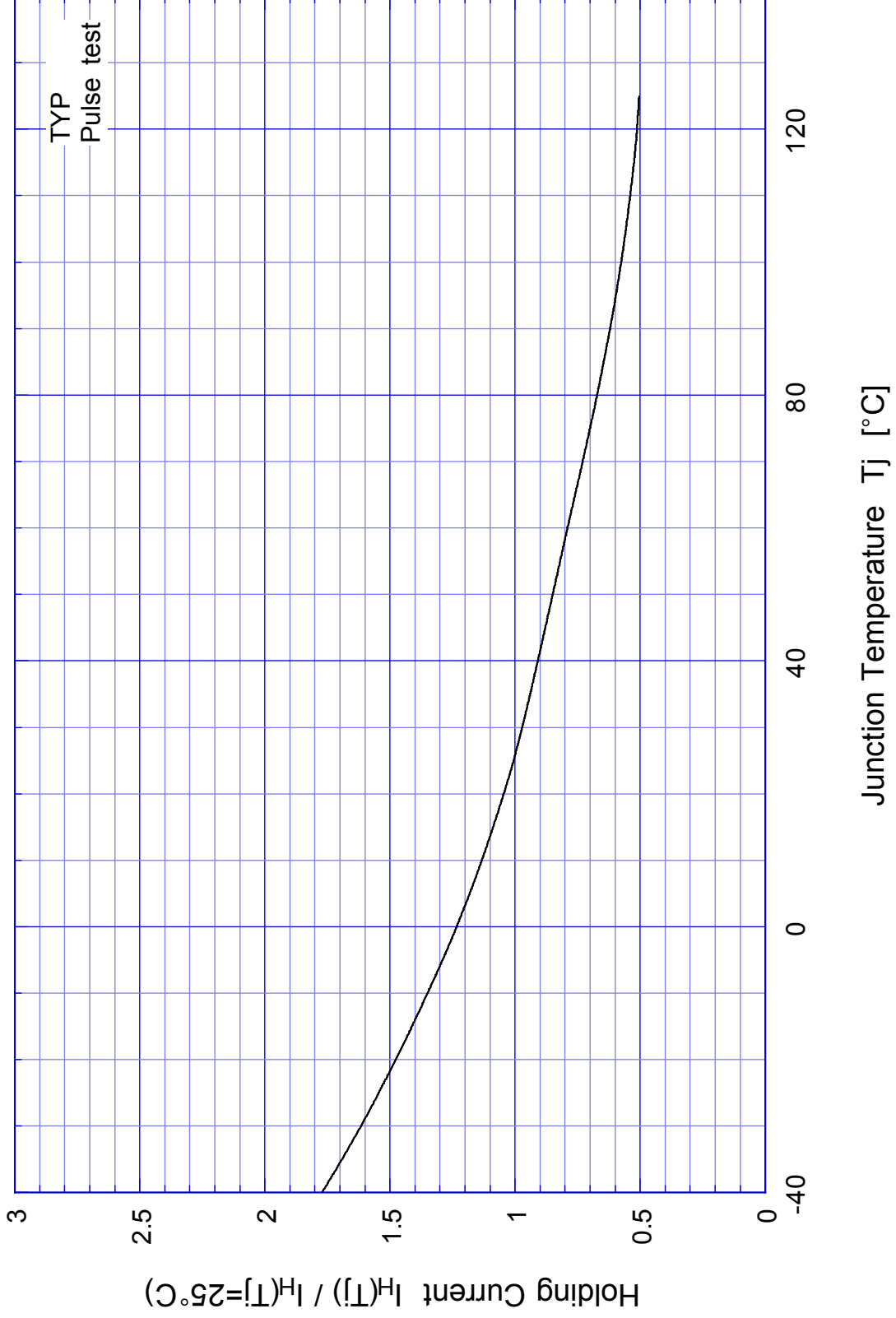
KP4N12 On-State Voltage - On-State Current



# KP4N12 Breakover Voltage - Junction Temperature

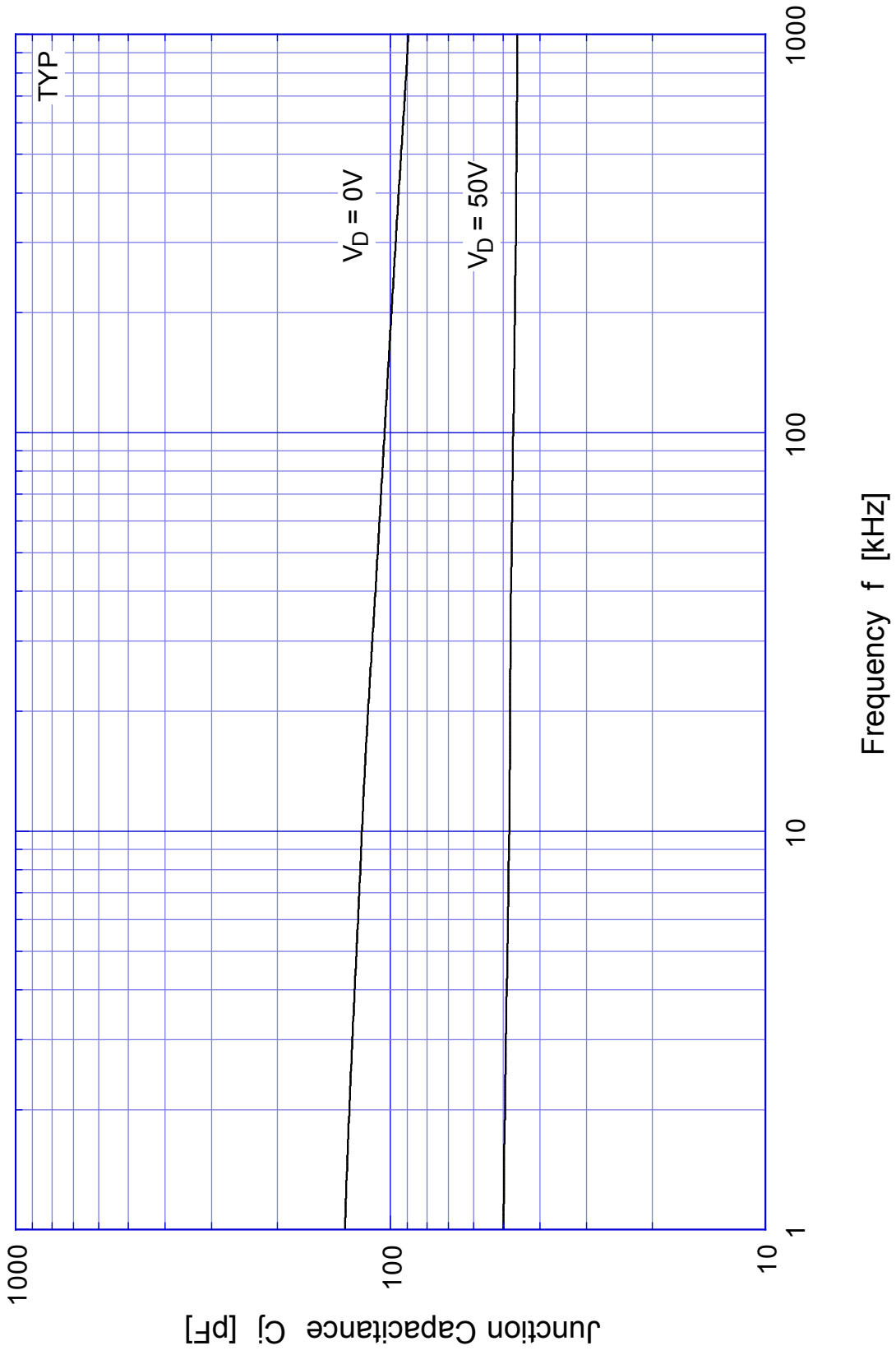


# KP4N12 Holding Current - Junction Temperature

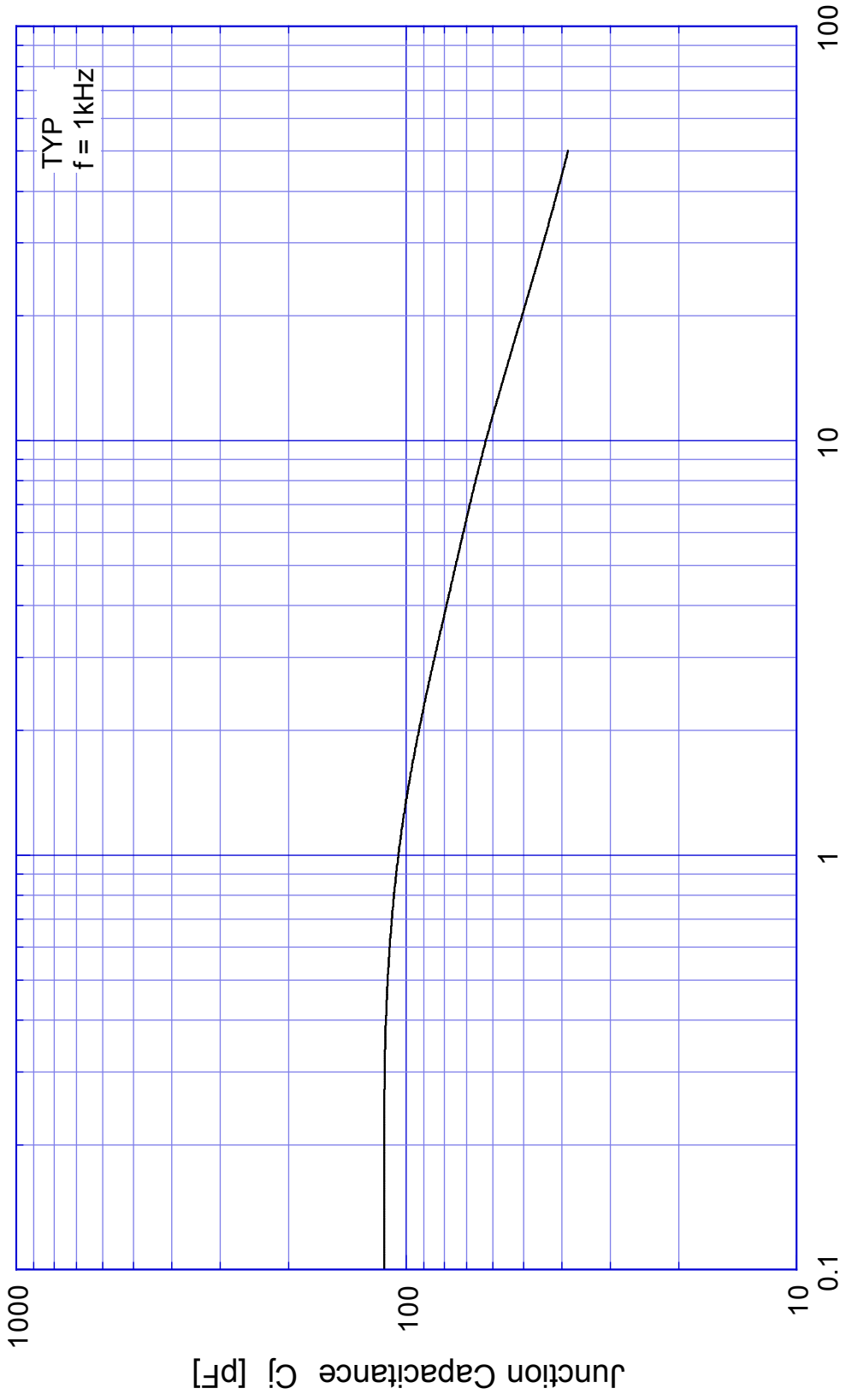


# KP4N12

## Junction Capacitance



# KP4N12 Junction Capacitance



Off-State Applied Voltage  $V_D$  [V]